

NPN SILICON PLANAR MEDIUM POWER HIGH CURRENT TRANSISTOR

ZTX855

ISSUE 2 – MARCH 94

FEATURES

- * 150 Volt V_{CE0}
- * 4 Amps continuous current
- * Up to 10 Amps peak current
- * Very low saturation voltage
- * $P_{tot} = 1.2$ Watt



**E-Line
TO92 Compatible**

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	250	V
Collector-Emitter Voltage	V_{CEO}	150	V
Emitter-Base Voltage	V_{EBO}	6	V
Peak Pulse Current	I_{CM}	10	A
Continuous Collector Current	I_C	4	A
Practical Power Dissipation*	P_{totp}	1.58	W
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1.2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^{\circ}C$

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	250	375		V	$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CER}$	250	375		V	$I_C=1\mu A, R_B \leq 1K\Omega$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	150	180		V	$I_C=10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	8		V	$I_E=100\mu A$
Collector Cut-Off Current	I_{CBO}			50 1	nA μA	$V_{CB}=200V$ $V_{CB}=200V, T_{amb}=100^{\circ}C$
Collector Cut-Off Current	I_{CER} $R \leq 1K\Omega$			50 1	nA μA	$V_{CB}=200V$ $V_{CB}=200V, T_{amb}=100^{\circ}C$
Emitter Cut-Off Current	I_{EBO}			10	nA	$V_{EB}=6V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		20 35 60 210	40 60 100 260	mV mV mV mV	$I_C=100mA, I_B=5mA^*$ $I_C=500mA, I_B=50mA^*$ $I_C=1A, I_B=100mA^*$ $I_C=4A, I_B=400mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		960	1100	mV	$I_C=4A, I_B=400mA^*$

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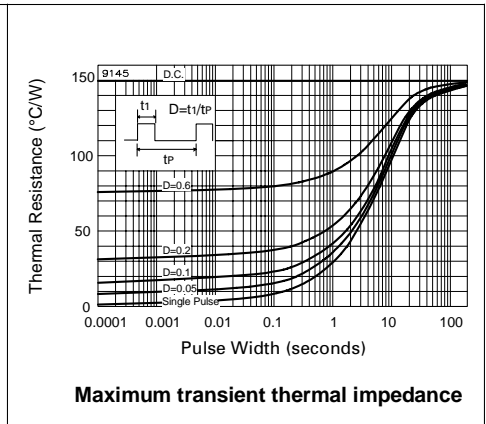
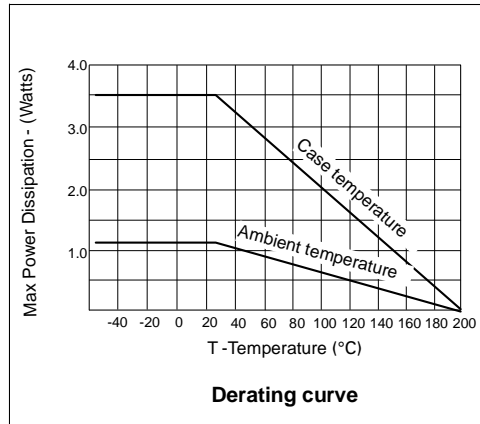
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		0.88	1	V	$I_C=4A, V_{CE}=5V^*$
Static Forward Current Transfer Ratio	h_{FE}	100 100 35	200 200 55 10	300		$I_C=10mA, V_{CE}=5V$ $I_C=1A, V_{CE}=5V^*$ $I_C=4A, V_{CE}=5V^*$ $I_C=10A, V_{CE}=5V^*$
Transition Frequency	f_T		90		MHz	$I_C=100mA, V_{CE}=10V$ $f=50MHz$
Output Capacitance	C_{obo}		22		pF	$V_{CB}=20V, f=1MHz$
Switching Times	t_{on} t_{off}		66 2130		ns ns	$I_C=1A, I_B=100mA$ $I_B=100mA, V_{CC}=50V$

*Measured under pulsed conditions. Pulse width=300 μ s. Duty cycle \leq 2%

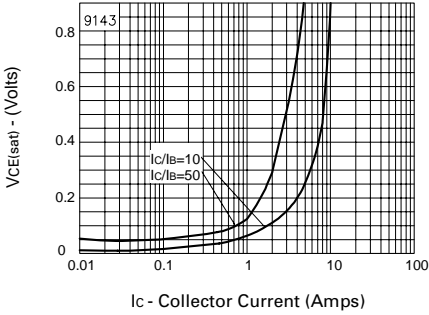
THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient Junction to Case	$R_{th(j-amb)}$ $R_{th(j-case)}$	150 50	$^{\circ}\text{C}/\text{W}$ $^{\circ}\text{C}/\text{W}$

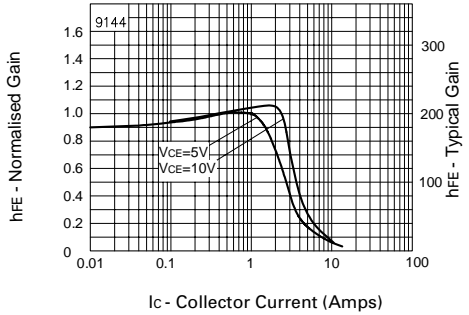


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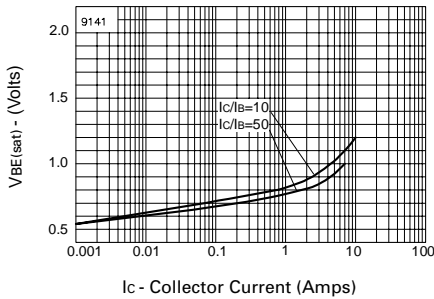
TYPICAL CHARACTERISTICS



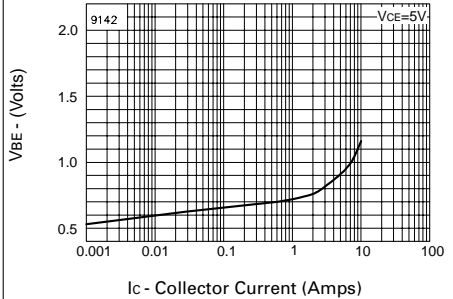
$V_{CE(sat)}$ v I_C



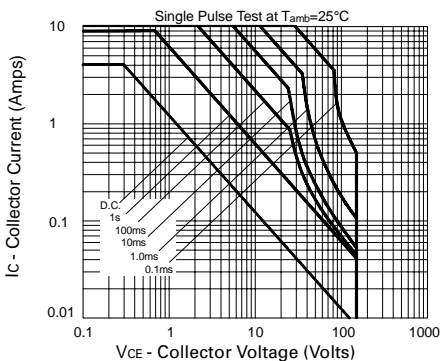
hFE v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



Safe Operating Area